

LMV321A-Q1 / LMV358A-Q1 / LMV324A-Q1 車載用低電圧レール・ツー・レール出力オペアンプ

1 特長

- 車載アプリケーション向けに AEC-Q100 認証済み
 - 温度グレード 1: -40°C ~ +125°C, TA
 - デバイス HBM ESD 分類レベル 2
 - デバイス CDM ESD 分類レベル C6
- 低入力オフセット電圧: ±1mV
- レール・ツー・レール出力
- ユニティ・ゲイン帯域幅: 1MHz
- 低広帯域ノイズ: 30nV/√Hz
- 低入力バイアス電流: 10pA
- 低い静止電流: 70µA/Ch
- ユニティ・ゲイン安定
- 内部 RFI および EMI フィルタ
- 最低 2.5V の電源電圧で動作
- 抵抗性の開ループ出力インピーダンスにより、大きな容量性負荷で簡単に安定
- 拡張温度範囲: -40°C ~ 125°C

2 アプリケーション

- AEC-Q100 グレード 1 アプリケーションに最適化
- インフォテインメントおよびクラスタ
- パッシブ型安全運転支援システム
- ボディ・エレクトロニクスおよび照明
- HEV/EV のインバータおよびモータ制御
- オンボード・チャージャ (OBC) およびワイヤレス・チャージャ
- パワートレイン電流センサ
- 先進運転支援システム (ADAS)
- 単一電源、ローサイド、単方向電流センシング回路

3 概要

LMV3xxA-Q1 ファミリーには、出力をレール・ツー・レールでシングリングできる、シングル (LMV321A-Q1)、デュアル (LMV358A-Q1)、クワッド・チャンネル (LMV324A-Q1) の低電圧 (2.5V ~ 5.5V) 車載用オペアンプがあります。これらのオペアンプは、インフォテインメントや照明など、低電圧での動作と大きな容量性負荷の駆動が必要で、スペースの制約が厳しいアプリケーション向けにコスト効率の優れた方法を提供します。LMV3xxA-Q1 ファミリーの容量性負荷の駆動能力は 500pF であり、オープン・ループ出力インピーダンスが抵抗性なので、はるかに大きな容量性負荷についても容易に安定化できます。これらのオペアンプは低電圧 (2.5V ~ 5.5V) で動作し、LMV3xx-Q1 デバイスと同様の性能仕様を満たすよう、特別に設計されています。

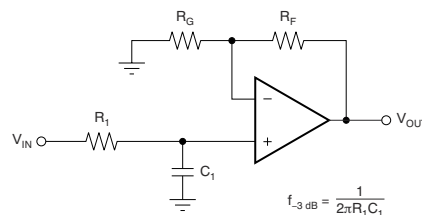
LMV3xxA-Q1 ファミリーは堅牢に設計されているため、回路設計を簡素化できます。これらのオペアンプには、ユニティ・ゲイン安定性、内蔵された RFI および EMI 除去フィルタ、オーバードライブ条件で位相反転が発生しないという特長があります。

LMV3xxA-Q1 ファミリーは、SOIC、MSOP、SOT-23、TSSOP などの業界標準パッケージで供給されます。

パッケージ情報 (1)

部品番号	パッケージ	本体サイズ (公称)
LMV321A-Q1	DBV (SOT-23, 5)	1.60mm x 2.90mm
	DCK (SC70, 5)	1.25mm x 2.00mm
LMV358A-Q1	D (SOIC, 8)	3.91mm x 4.90mm
	DGK (VSSOP, 8)	3.00mm x 3.00mm
LMV324A-Q1	D (SOIC, 14)	8.65mm x 3.91mm
	PW (TSSOP, 14)	4.40mm x 5.00mm
	DYY (SOT-23, 14)	4.20mm x 1.90mm

(1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1 C_1}\right)$$

単極ローパス・フィルタ



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (January 2023) to Revision D (April 2023)	Page
• DBV パッケージのステータスをプレビューからアクティブに変更	1

Changes from Revision B (October 2021) to Revision C (January 2023)	Page
• 「製品情報」表の SC70 (5) パッケージからプレビュー注記を削除	1
• Changed the formatting of the <i>Pin Configuration and Functions</i> section.....	3
• Changed values in <i>Thermal Information: LMV321A-Q1</i> table.....	6

Changes from Revision A (April 2021) to Revision B (October 2021)	Page
• データシートに LMV321A-Q1 GPN を追加.....	1
• 「製品情報」表に SOT-23 (5) および SC70 (5) パッケージを追加	1
• 「製品情報」表の SOT-23 (14) および TSSOP (14) パッケージからプレビュー注記を削除	1
• Added LMV321A-Q1 SOT-23 (5), SC70 (5), and LMV321AU-Q1 SOT-23 (5) Packages, to <i>Pin Configuration and Functions</i> section.....	3
• Added <i>Thermal Information: LMV321A-Q1</i> table.....	6

Changes from Revision * (June 2020) to Revision A (April 2021)	Page
• 文書全体にわたって表、図、相互参照の採番方法を更新.....	1
• 「製品情報」表の VSSOP (8) パッケージからプレビュー注記を削除	1
• 「製品情報」表から SOT-23 (8)、TSSOP (8)、SOT-23 (5)、SC70 (5) パッケージを削除	1
• Deleted TSSOP (8) Package, from <i>Pin Configuration and Functions</i> section.....	3
• Added note (4) to differential input voltage in <i>Absolute Maximum Ratings</i> table.....	5
• Added thermal information for DGK package.....	6
• Added thermal information for DYY package.....	6

5 Pin Configuration and Functions

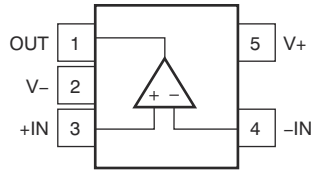


图 5-1. LMV321A-Q1 DBV Package,
5-Pin SOT-23
(Top View)

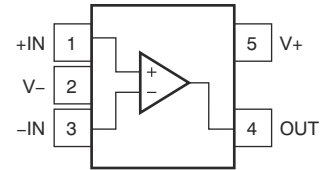


图 5-2. LMV321A-Q1 DCK, LMV321AU-Q1 DBV
Package,
5-Pin SC70, SOT-23
(Top View)

表 5-1. Pin Functions: LMV321A-Q1

NAME	PIN		TYPE (1)	DESCRIPTION
	DBV	DCK, DBV (U)		
-IN	4	3	I	Inverting input
+IN	3	1	I	Non-inverting input
OUT	1	4	O	Output
V-	2	2	—	Negative (lowest) supply or ground (for single-supply operation)
V+	5	5	—	Positive (highest) supply

(1) I = input, O = output

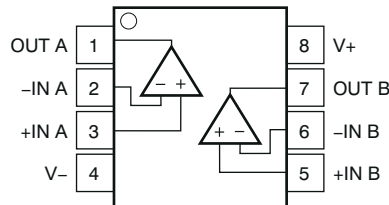
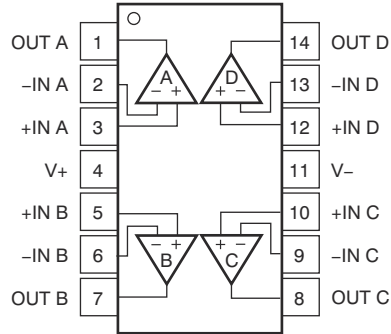


图 5-3. LMV358A-Q1 D and DGK Packages,
8-Pin SOIC and VSSOP
(Top View)

表 5-2. Pin Functions: LMV358A-Q1

NAME	PIN		TYPE ⁽¹⁾	DESCRIPTION
	NO.			
-IN A	2		I	Inverting input, channel A
+IN A	3		I	Non-inverting input, channel A
-IN B	6		I	Inverting input, channel B
+IN B	5		I	Non-inverting input, channel B
OUT A	1		O	Output, channel A
OUT B	7		O	Output, channel B
V-	4		—	Negative (lowest) supply or ground (for single-supply operation)
V+	8		—	Positive (highest) supply

(1) I = input, O = output



**图 5-4. LMV324A-Q1 D, PW, and DYY Packages,
 14-Pin SOIC, TSSOP, and SOT-23
 (Top View)**

表 5-3. Pin Functions: LMV324A-Q1

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
-IN A	2	I	Inverting input, channel A
+IN A	3	I	Non-inverting input, channel A
-IN B	6	I	Inverting input, channel B
+IN B	5	I	Non-inverting input, channel B
-IN C	9	I	Inverting input, channel C
+IN C	10	I	Non-inverting input, channel C
-IN D	13	I	Inverting input, channel D
+IN D	12	I	Non-inverting input, channel D
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
OUT C	8	O	Output, channel C
OUT D	14	O	Output, channel D
V-	11	—	Negative (lowest) supply or ground (for single-supply operation)
V+	4	—	Positive (highest) supply

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
Supply voltage, (V ₊ – V _–)		0	6	V	
Signal input pins	Voltage ⁽²⁾	Common-mode	(V _–) – 0.5	(V ₊) + 0.5	V
		Differential ⁽⁴⁾	(V ₊) – (V _–) + 0.2		V
	Current ⁽²⁾	–10	10	mA	
Output short-circuit ⁽³⁾		Continuous			
Operating, T _A		–55	150	°C	
Operating junction temperature, T _J			150	°C	
Storage temperature, T _{stg}		–65	150	°C	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.
- (4) Differential input voltages greater than 0.5 V applied continuously can result in a shift to the input offset voltage and quiescent current above the maximum specifications of these parameters. The magnitude of this effect increases as the ambient operating temperature rises.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level C5	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with ANSI/ESDA/JEDEC JS-001 Specification

6.3 Recommended Operating Conditions

over operating temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _S	Supply voltage	2.5	5.5	V
T _A	Specified temperature	–40	125	°C

6.4 Thermal Information: LMV321A-Q1

THERMAL METRIC ⁽¹⁾		LMV321A-Q1		UNIT
		DBV (SOT-23)	DCK (SC70)	
		5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	232.5	246.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	131.0	157.5	°C/W
R _{θJB}	Junction-to-board thermal resistance	99.6	95.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	66.5	68.8	°C/W
ψ _{JB}	Junction-to-board characterization parameter	99.1	95.0	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

6.5 Thermal Information: LMV358A-Q1

THERMAL METRIC ⁽¹⁾		LMV358A-Q1		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	151.9	196.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	92.0	86.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	95.4	118.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	40.2	23.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	94.7	116.7	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

6.6 Thermal Information: LMV324A-Q1

THERMAL METRIC ⁽¹⁾		LMV324A-Q1			UNIT
		D (SOIC)	PW (TSSOP)	DYY (SOT-23)	
		14 PINS	14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	115.1	135.3	154.3	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	71.2	63.5	86.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	71.1	78.4	67.9	°C/W
ψ _{JT}	Junction-to-top characterization parameter	29.6	13.6	10.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	70.7	77.9	67.5	°C/W

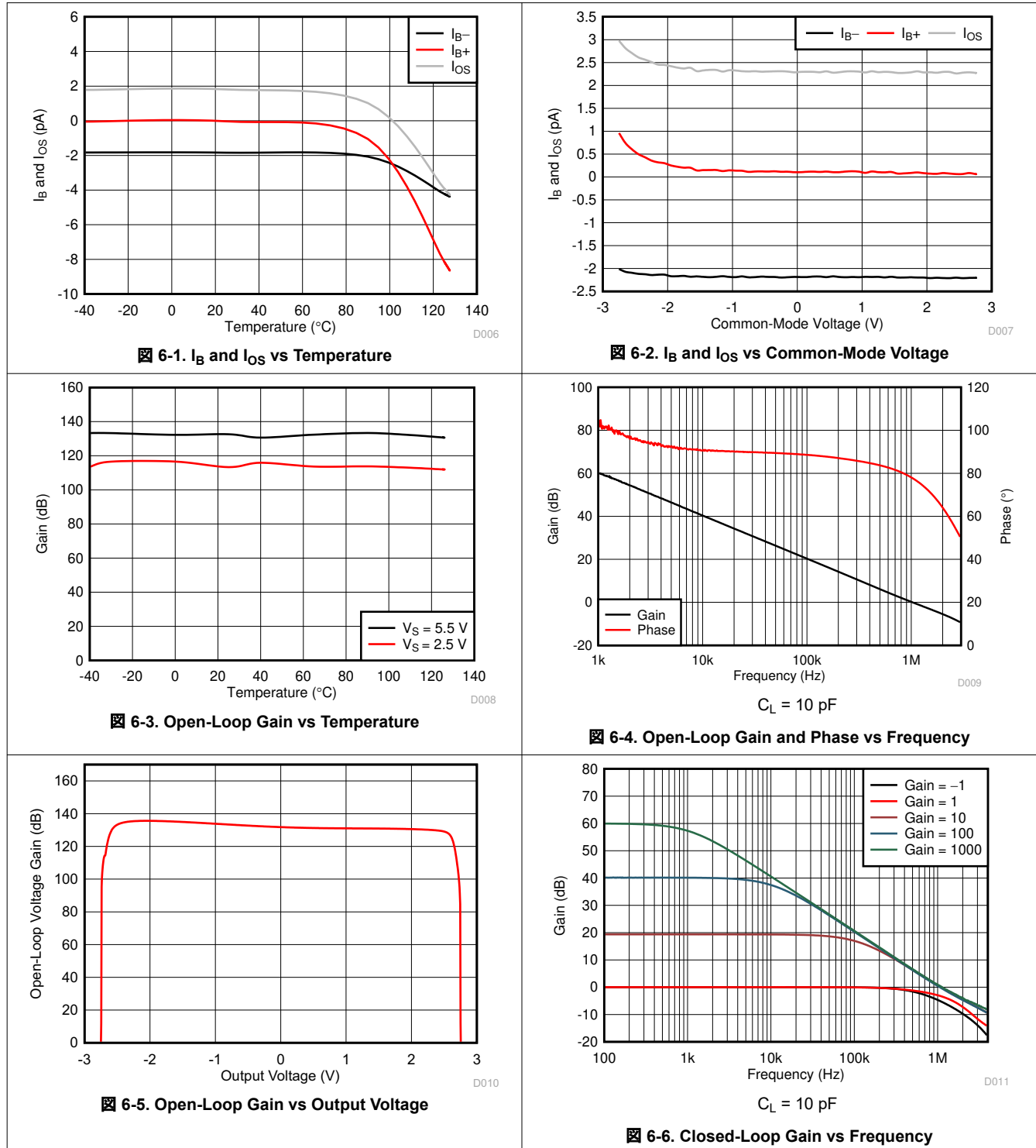
6.7 Electrical Characteristics

For $V_S = (V_+) - (V_-) = 2.5\text{ V to }5.5\text{ V}$ ($\pm 0.9\text{ V to } \pm 2.75\text{ V}$), $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V_{OS}	Input offset voltage	$V_S = 5\text{ V}$		± 1	± 4	mV
		$V_S = 5\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$			± 5	
dV_{OS}/dT	V_{OS} vs temperature	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		± 1		$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$V_S = 2.5\text{ to }5.5\text{ V}$, $V_{CM} = (V_-)$	78	100		dB
INPUT VOLTAGE RANGE						
V_{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	$(V_-) - 0.1$		$(V_+) - 1$	V
CMRR	Common-mode rejection ratio	$V_S = 2.5\text{ V}$, $(V_-) - 0.1\text{ V} < V_{CM} < (V_+) - 1.4\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		86		dB
		$V_S = 5.5\text{ V}$, $(V_-) - 0.1\text{ V} < V_{CM} < (V_+) - 1.4\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		95		
		$V_S = 5.5\text{ V}$, $(V_-) - 0.1\text{ V} < V_{CM} < (V_+) + 0.1\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$	63	77		
		$V_S = 2.5\text{ V}$, $(V_-) - 0.1\text{ V} < V_{CM} < (V_+) + 0.1\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		68		
INPUT BIAS CURRENT						
I_B	Input bias current	$V_S = 5\text{ V}$		± 10		pA
I_{OS}	Input offset current			± 3		pA
NOISE						
E_n	Input voltage noise (peak-to-peak)	$f = 0.1\text{ Hz to }10\text{ Hz}$, $V_S = 5\text{ V}$		5.1		μV_{PP}
e_n	Input voltage noise density	$f = 1\text{ kHz}$, $V_S = 5\text{ V}$		33		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$, $V_S = 5\text{ V}$		30		
i_n	Input current noise density	$f = 1\text{ kHz}$, $V_S = 5\text{ V}$		25		$\text{fA}/\sqrt{\text{Hz}}$
INPUT CAPACITANCE						
C_{ID}	Differential			1.5		pF
C_{IC}	Common-mode			5		pF
OPEN-LOOP GAIN						
A_{OL}	Open-loop voltage gain	$V_S = 5.5\text{ V}$, $(V_-) + 0.05\text{ V} < V_O < (V_+) - 0.05\text{ V}$, $R_L = 10\text{ k}\Omega$	100	115		dB
		$V_S = 2.5\text{ V}$, $(V_-) + 0.04\text{ V} < V_O < (V_+) - 0.04\text{ V}$, $R_L = 10\text{ k}\Omega$		98		
		$V_S = 2.5\text{ V}$, $(V_-) + 0.1\text{ V} < V_O < (V_+) - 0.1\text{ V}$, $R_L = 2\text{ k}\Omega$		112		
		$V_S = 5.5\text{ V}$, $(V_-) + 0.15\text{ V} < V_O < (V_+) - 0.15\text{ V}$, $R_L = 2\text{ k}\Omega$		128		
FREQUENCY RESPONSE						
GBW	Gain-bandwidth product	$V_S = 5\text{ V}$		1		MHz
Φ_m	Phase margin	$V_S = 5.5\text{ V}$, $G = 1$		76		$^\circ$
SR	Slew rate	$V_S = 5\text{ V}$		1.7		V/ μs
t_s	Settling time	To 0.1%, $V_S = 5\text{ V}$, 2-V step, $G = +1$, $C_L = 100\text{ pF}$		3		μs
		To 0.01%, $V_S = 5\text{ V}$, 2-V step, $G = +1$, $C_L = 100\text{ pF}$		4		
t_{OR}	Overload recovery time	$V_S = 5\text{ V}$, $V_{IN} \times \text{gain} > V_S$		0.9		μs
THD+N	Total harmonic distortion + noise	$V_S = 5.5\text{ V}$, $V_{CM} = 2.5\text{ V}$, $V_O = 1\text{ V}_{RMS}$, $G = +1$, $f = 1\text{ kHz}$, 80-kHz measurement BW		0.005%		
OUTPUT						
V_O	Voltage output swing from supply rails	$V_S = 5.5\text{ V}$, $R_L = 10\text{ k}\Omega$		20	50	mV
		$V_S = 5.5\text{ V}$, $R_L = 2\text{ k}\Omega$		40	75	
I_{SC}	Short-circuit current	$V_S = 5.5\text{ V}$		± 40		mA
Z_O	Open-loop output impedance	$V_S = 5\text{ V}$, $f = 1\text{ MHz}$		1200		Ω
POWER SUPPLY						
V_S	Specified voltage range		2.5 (± 1.25)		5.5 (± 2.75)	V
I_Q	Quiescent current per amplifier	$I_O = 0\text{ mA}$, $V_S = 5.5\text{ V}$		70	125	μA
		$I_O = 0\text{ mA}$, $V_S = 5.5\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$			150	
	Power-on time	$V_S = 0\text{ V to }5\text{ V}$, to 90% I_Q level		50		μs

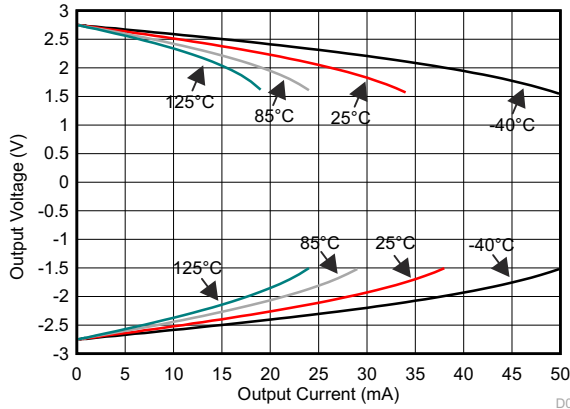
6.8 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

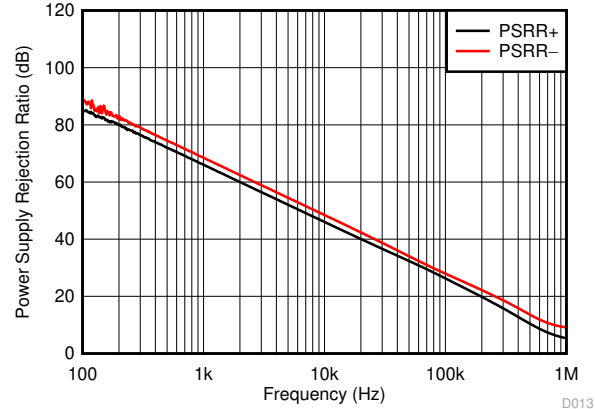


6.8 Typical Characteristics (continued)

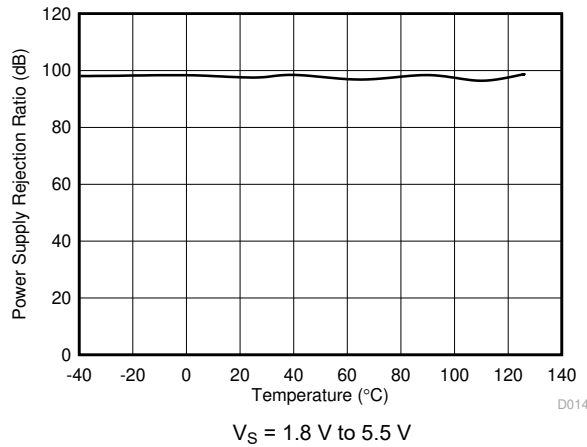
at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



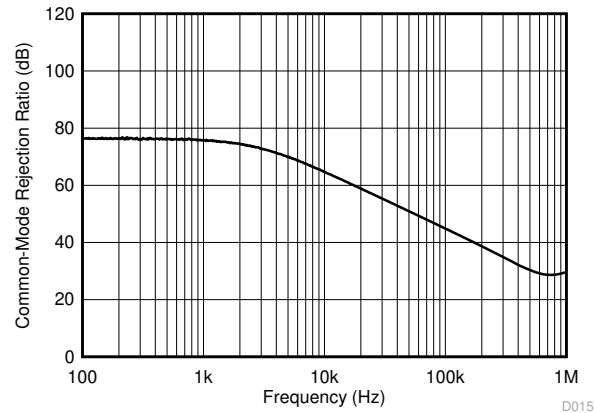
6-7. Output Voltage vs Output Current (Claw)



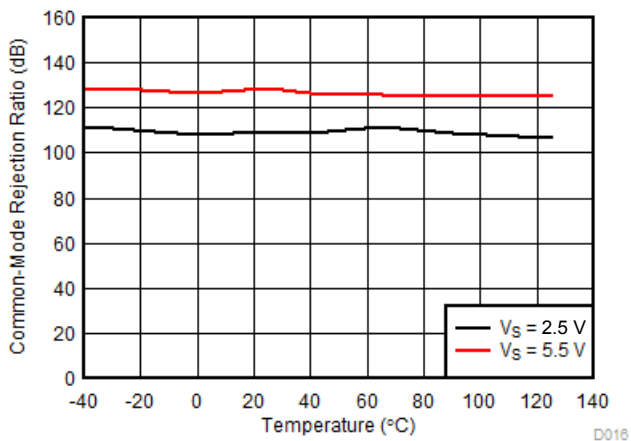
6-8. PSRR vs Frequency



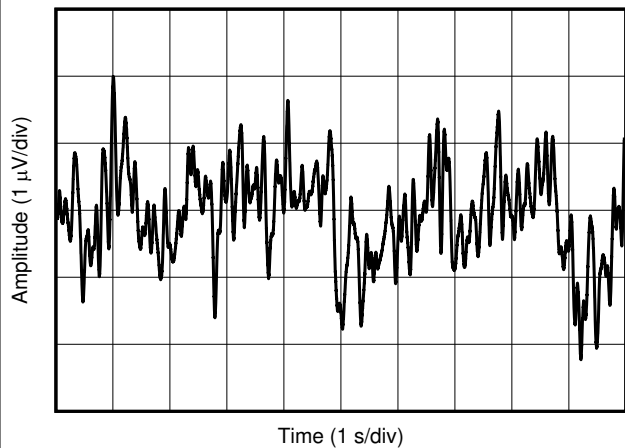
6-9. DC PSRR vs Temperature



6-10. CMRR vs Frequency



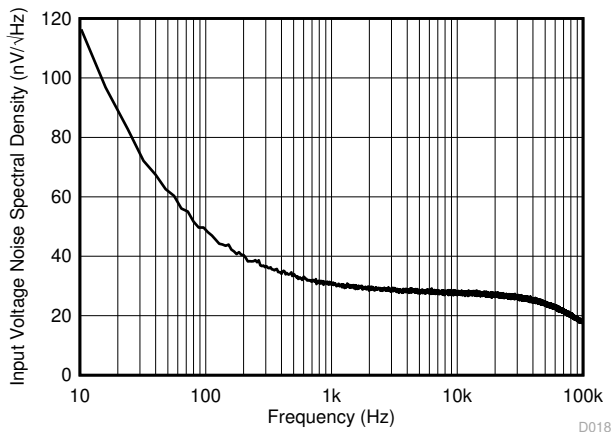
6-11. DC CMRR vs Temperature



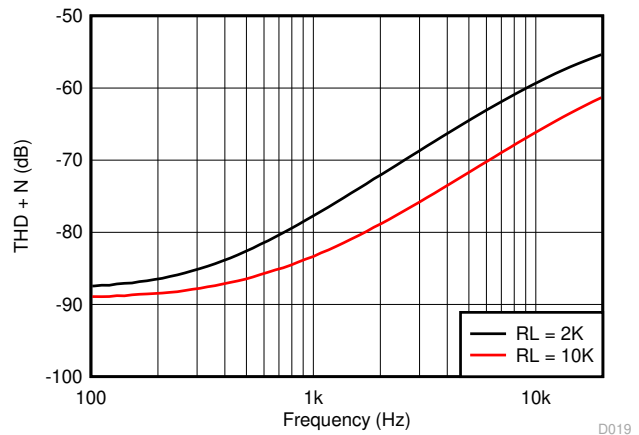
6-12. 0.1 Hz to 10 Hz Integrated Voltage Noise

6.8 Typical Characteristics (continued)

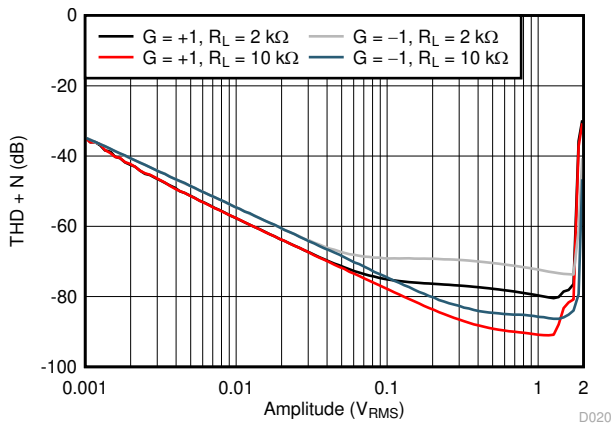
at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



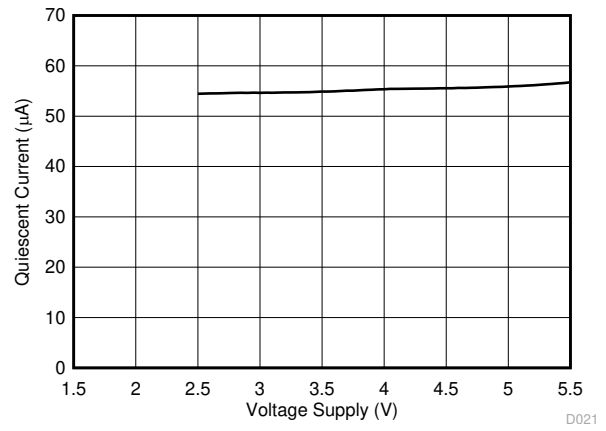
6-13. Input Voltage Noise Spectral Density



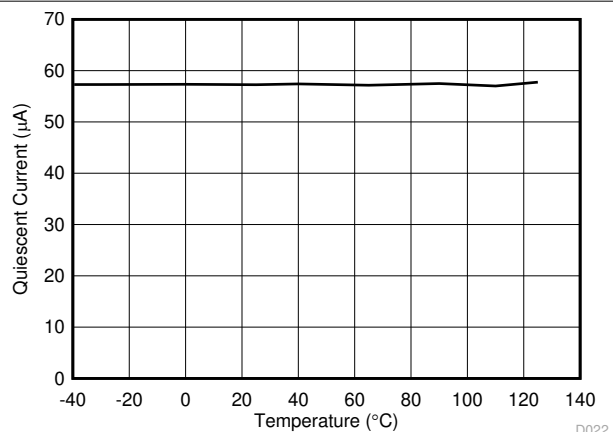
6-14. THD + N vs Frequency
 $V_S = 5.5\text{ V}$, $V_{CM} = 2.5\text{ V}$, $G = 1$, $BW = 80\text{ kHz}$, $V_{OUT} = 0.5\text{ V}_{RMS}$



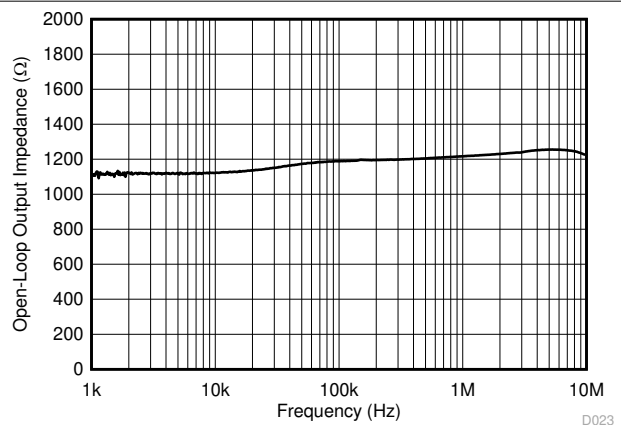
6-15. THD + N vs Amplitude
 $V_S = 5.5\text{ V}$, $V_{CM} = 2.5\text{ V}$, $f = 1\text{ kHz}$, $G = 1$, $BW = 80\text{ kHz}$



6-16. Quiescent Current vs Supply Voltage



6-17. Quiescent Current vs Temperature



6-18. Open-Loop Output Impedance vs Frequency

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

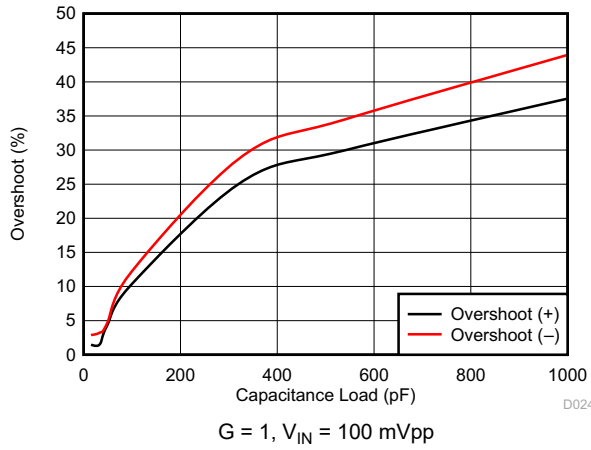


图 6-19. Small Signal Overshoot vs Capacitive Load

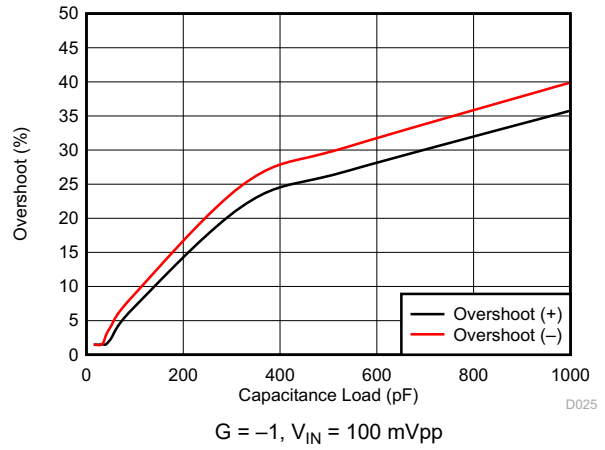


图 6-20. Small Signal Overshoot vs Capacitive Load

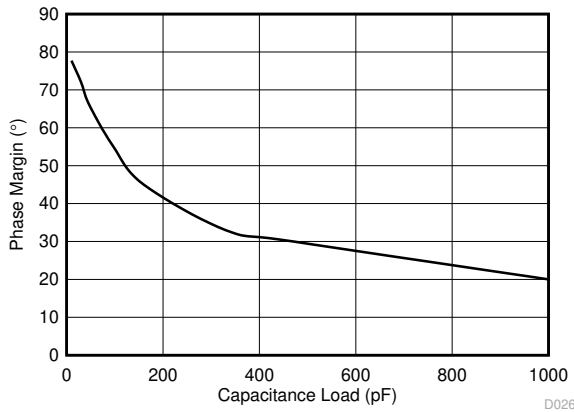


图 6-21. Phase Margin vs Capacitive Load

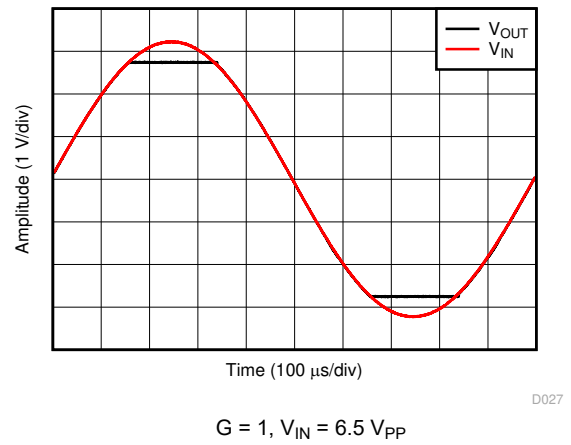


图 6-22. No Phase Reversal

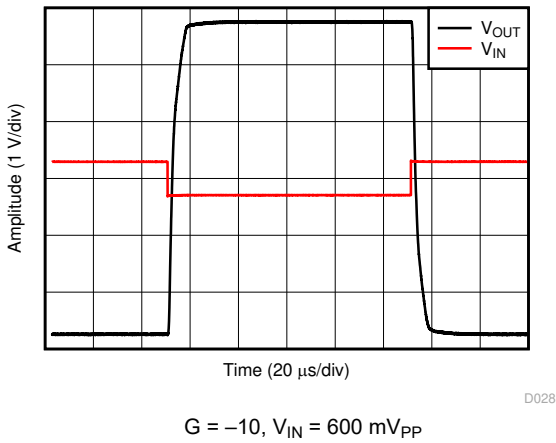


图 6-23. Overload Recovery

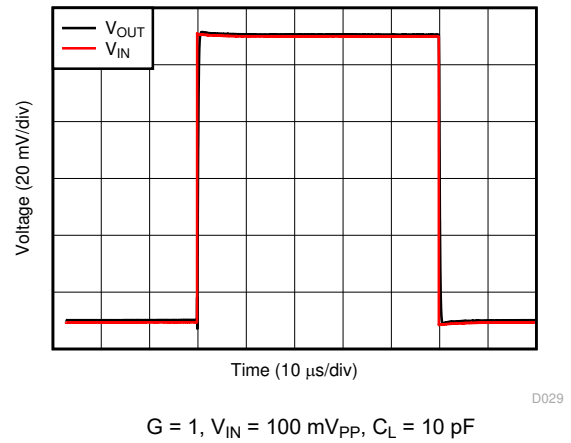
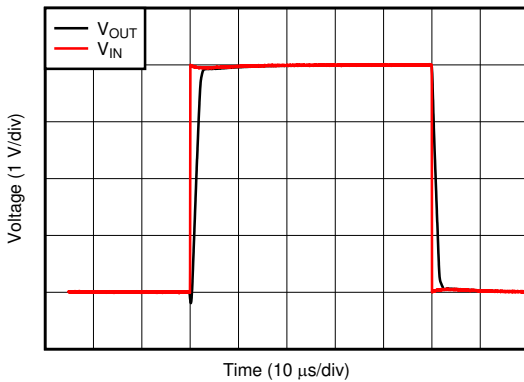


图 6-24. Small-Signal Step Response

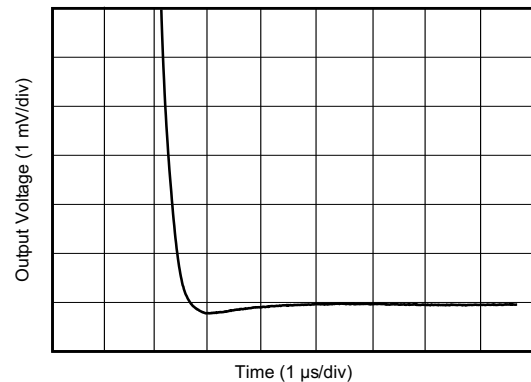
6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



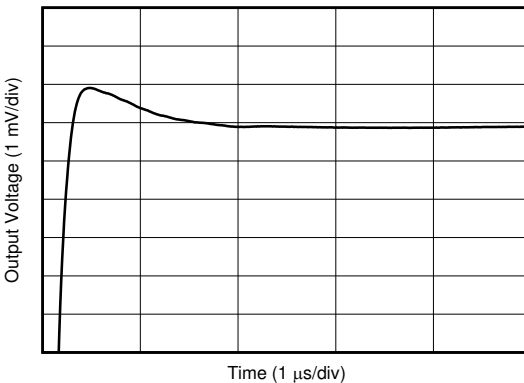
$G = 1$, $V_{IN} = 4\text{ V}_{PP}$, $C_L = 10\text{ pF}$

6-25. Large-Signal Step Response



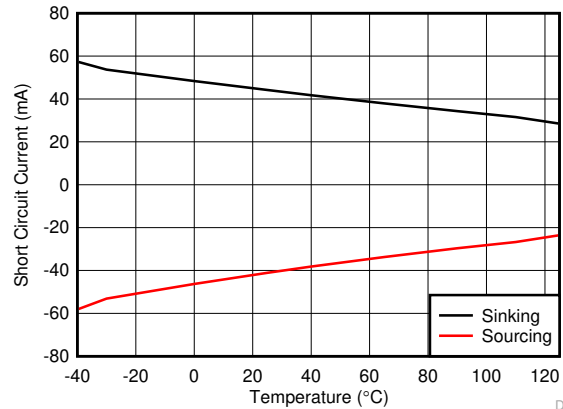
$G = 1$, $C_L = 100\text{ pF}$, 2-V step

6-26. Large-Signal Settling Time (Negative)

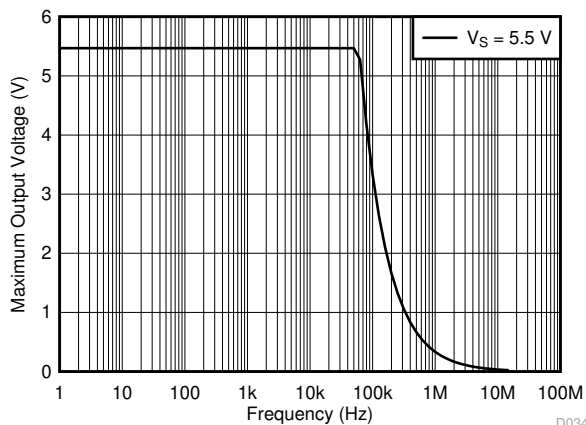


$G = 1$, $C_L = 100\text{ pF}$, 2-V step

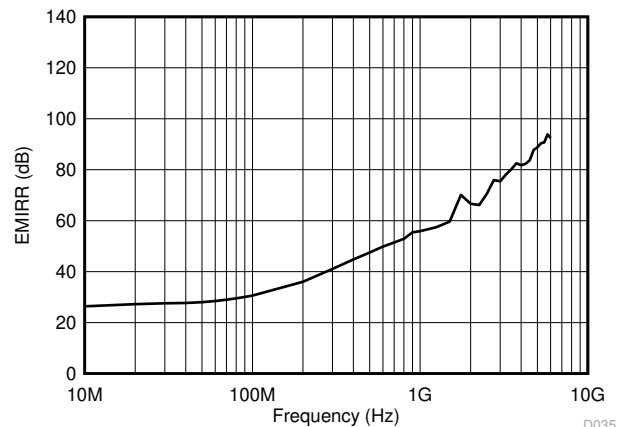
6-27. Large-Signal Settling Time (Positive)



6-28. Short-Circuit Current vs Temperature



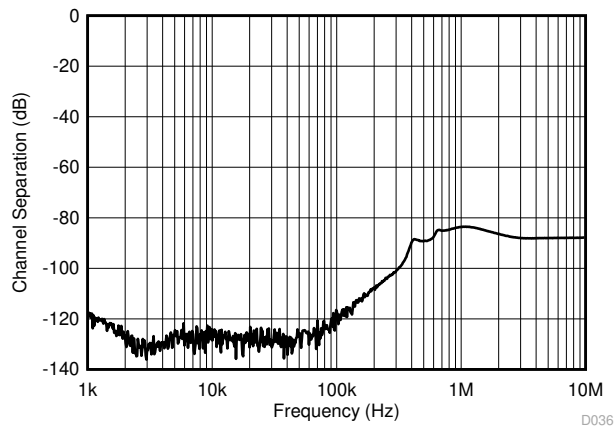
6-29. Maximum Output Voltage vs Frequency



6-30. Electromagnetic Interference Rejection Ratio Referred to Non-inverting Input (EMIRR+) vs Frequency

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



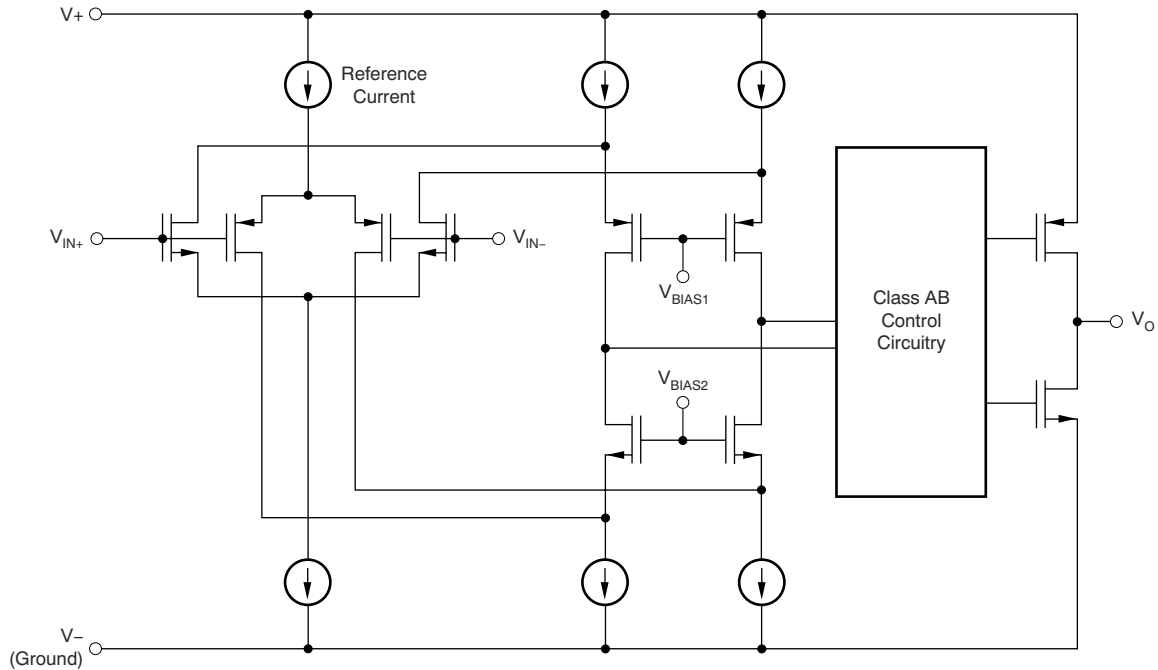
6-31. Channel Separation

7 Detailed Description

7.1 Overview

The LMV3xxA-Q1 is a family of low-power, rail-to-rail output op amps. These devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes the negative rail and allows the LMV3xxA-Q1 family to be used in many single-supply applications. Rail-to-rail output swing significantly increases dynamic range, especially in low-supply applications, and makes the family of devices an excellent choice for driving sampling analog-to-digital converters (ADCs).

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Operating Voltage

The LMV3xxA-Q1 family of op amps are for operation from 2.5 V to 5.5 V. In addition, many specifications such as input offset voltage, quiescent current, offset current, and short circuit current apply from -40°C to 125°C . Parameters that vary significantly with operating voltages or temperature are shown in the [Typical Characteristics](#) section.

7.3.2 Input Common Mode Range

The input common-mode voltage range of the LMV3xxA-Q1 family extends 100 mV beyond the negative supply rail and within 1 V below the positive rail for the full supply voltage range of 2.5 V to 5.5 V. This performance is achieved with a P-channel differential pair, as shown in the [Functional Block Diagram](#). Additionally, a complementary N-channel differential pair has been included in parallel to eliminate issues with phase reversal that are common with previous generations of op amps. However, the N-channel pair is not optimized for operation. TI recommends limiting any voltages applied at the inputs to less than $V_{CC} - 1\text{ V}$ to make sure that the op amp conforms to the specifications detailed in the [Electrical Characteristics](#) table.

7.3.3 Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the LMV3xxA-Q1 family delivers a robust output drive capability. A class-AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10 k Ω , the output swings to within 20 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

7.3.4 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return to the linear state. After the charge carriers return to the linear state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the LMV3xxA-Q1 family is approximately 850 ns.

7.4 Device Functional Modes

The LMV3xxA-Q1 family has a single functional mode. The devices are powered on as long as the power-supply voltage is between 2.5 V ($\pm 1.25\text{ V}$) and 5.5 V ($\pm 2.75\text{ V}$).

8 Application and Implementation

注


以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくこととなります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

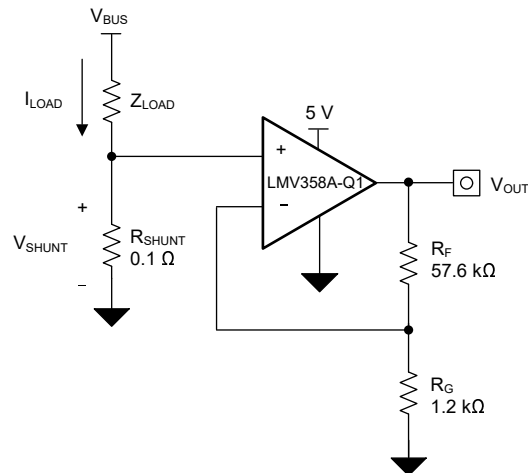
8.1 Application Information

The LMV3xxA-Q1 family of low-power, rail-to-rail output operational amplifiers is specifically designed for portable applications. The devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for for a wide range of general-purpose applications. The class AB output stage is capable of driving less than or equal to 10-k Ω loads connected to any point between V+ and V-. The input common-mode voltage range includes the negative rail, and allows the LMV3xxA-Q1 devices to be used in many single-supply applications.

8.2 Typical Application

8.2.1 LMV3xxA-Q1 Low-Side, Current Sensing Application

 8-1 shows the LMV3xxA-Q1 configured in a low-side current sensing application.



 8-1. LMV3xxA-Q1 in a Low-Side, Current-Sensing Application

8.2.1.1 Design Requirements

The design requirements for this design are:

- Load current: 0 A to 1 A
- Output voltage: 4.9 V
- Maximum shunt voltage: 100 mV

8.2.1.2 Detailed Design Procedure

The transfer function of the circuit in [Figure 8-1](#) is given in [Equation 1](#).

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain \quad (1)$$

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest shunt resistor is shown using [Equation 2](#).

$$R_{SHUNT} = \frac{V_{SHUNT_MAX}}{I_{LOAD_MAX}} = \frac{100\text{ mV}}{1\text{ A}} = 100\text{ m}\Omega \quad (2)$$

Using [Equation 2](#), R_{SHUNT} is calculated to be 100 m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the LMV3xxA-Q1 to produce an output voltage of approximately 0 V to 4.9 V. The gain needed by the LMV3xxA-Q1 to produce the necessary output voltage is calculated using [Equation 3](#).

$$Gain = \frac{(V_{OUT_MAX} - V_{OUT_MIN})}{(V_{IN_MAX} - V_{IN_MIN})} \quad (3)$$

Using [Equation 3](#), the required gain is calculated to be 49 V/V, which is set with resistors R_F and R_G . [Equation 4](#) sizes the resistors R_F and R_G , to set the gain of the LMV3xxA-Q1 to 49 V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)} \quad (4)$$

Selecting R_F as 57.6 k Ω and R_G as 1.2 k Ω provides a combination that equals 49 V/V. [Figure 8-2](#) shows the measured transfer function of the circuit shown in [Figure 8-1](#). Notice that the gain is only a function of the feedback and gain resistors. This gain is adjusted by varying the ratio of the resistors and the actual resistors values are determined by the impedance levels that the designer wants to establish. The impedance level determines the current drain, the effect that stray capacitance has, and a few other behaviors. There is no best impedance selection that works for every system, choose an impedance that is an excellent choice for the system parameters.

8.2.1.3 Application Curve

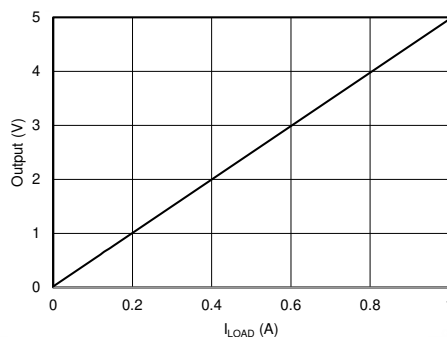
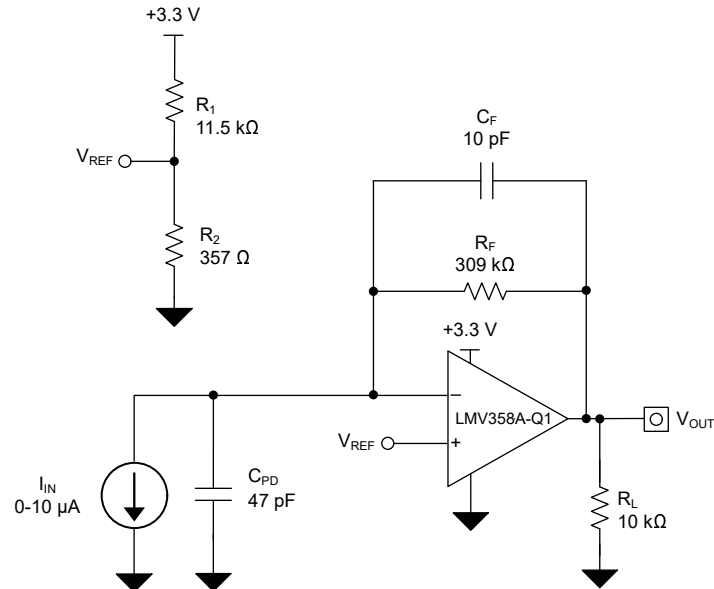


Figure 8-2. Low-Side, Current-Sense Transfer Function

8.2.2 Single-Supply Photodiode Amplifier

Photodiodes are used in many applications to convert light signals to electrical signals. The current through the photodiode is proportional to the photon energy absorbed, and is commonly in the range of a few hundred picoamps to a few tens of microamps. An amplifier in a transimpedance configuration is typically used to convert the low-level photodiode current to a voltage signal for processing in an MCU. The circuit shown in [8-3](#) is an example of a single-supply photodiode amplifier circuit using the LMV358A-Q1.



8-3. Single-Supply Photodiode Amplifier Circuit

8.2.2.1 Design Requirements

The design requirements for this design are:

- Supply voltage: 3.3 V
- Input: 0 μA to 10 μA
- Output: 0.1 V to 3.2 V
- Bandwidth: 50 kHz

8.2.2.2 Detailed Design Procedure

The transfer function between the output voltage (V_{OUT}), the input current, (I_{IN}) and the reference voltage (V_{REF}) is defined in 式 5.

$$V_{OUT} = I_{IN} + R_F + V_{REF} \quad (5)$$

Where:

$$V_{REF} = V_+ \times \left(\frac{R_1 \times R_2}{R_1 + R_2} \right) \quad (6)$$

Set V_{REF} to 100 mV to meet the minimum output voltage level by setting R1 and R2 to meet the required ratio calculated in 式 7.

$$\frac{V_{REF}}{V_+} = \frac{0.1V}{3.3V} = 0.0303 \quad (7)$$

The closest resistor ratio to meet this ratio sets R1 to 11.5 kΩ and R2 to 357 Ω.

The required feedback resistance can be calculated based on the input current and desired output voltage.

$$R_F = \frac{V_{OUT} - V_{REF}}{I_{IN}} = \frac{3.2V - 0.1V}{10\mu A} = 310 \frac{kV}{A} \approx 309 k\Omega \quad (8)$$

Calculate the value for the feedback capacitor based on R_F and the desired –3-dB bandwidth, (f_{-3dB}) using 式 9.

$$C_F = \frac{1}{2 \times \pi \times R_F \times f_{-3dB}} = \frac{1}{2 \times \pi \times 309k\Omega \times 50kHz} = 10.3 pF \approx 10 pF \quad (9)$$

The minimum op amp bandwidth required for this application is based on the value of R_F , C_F , and the capacitance on the INx– pin of the LMV358A-Q1 which is equal to the sum of the photodiode shunt capacitance, (CPD) the common-mode input capacitance, (CCM) and the differential input capacitance (CD) as 式 10 shows.

$$C_{IN} = C_{PD} + C_{CM} + C_D = 47 pF + 5 pF + 1 pF = 53 pF \quad (10)$$

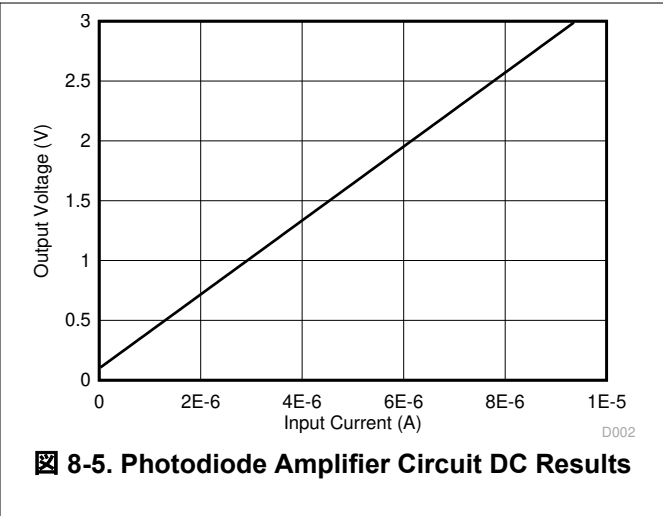
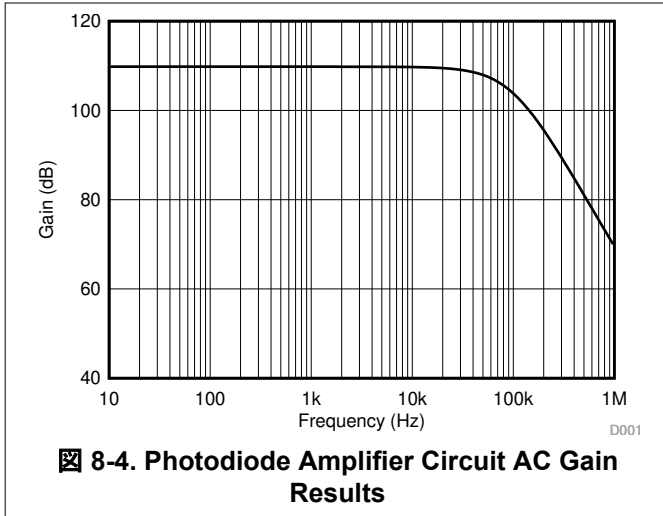
The minimum op amp bandwidth is calculated in 式 11.

$$F = BGW \geq \frac{C_{IN} + C_F}{2 \times \pi \times R_F \times C_F} \geq 324 kHz \quad (11)$$

The 1-MHz bandwidth of the LMV3xxA-Q1 meets the minimum bandwidth requirement and remains stable in this application configuration.

8.2.2.3 Application Curves

The measured current-to-voltage transfer function for the photodiode amplifier circuit is shown in [8-4](#). The measured performance of the photodiode amplifier circuit is shown in [8-5](#).



9 Power Supply Recommendations

The LMV3xxA-Q1 family is specified for operation from 2.5 V to 5.5 V (± 1.25 V to ± 2.75 V); many specifications apply from -40°C to 125°C . The [Typical Characteristics](#) section presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

注意

Supply voltages larger than 6 V may permanently damage the device; see the [Absolute Maximum Ratings](#) table.

Place 0.1- μF bypass capacitors close to the power-supply pins to reduce coupling errors from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the [Layout Guidelines](#) section.

9.1 Input and ESD Protection

The LMV3xxA-Q1 family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA. [Figure 9-1](#) shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

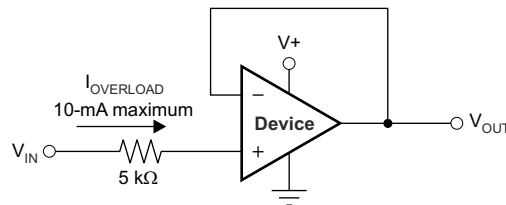



Figure 9-1. Input Current Protection

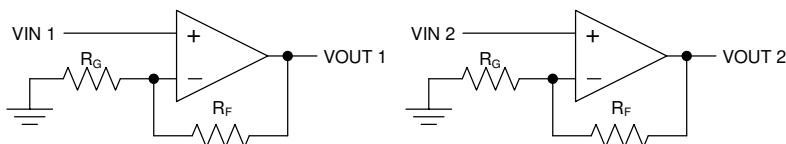
10 Layout

10.1 Layout Guidelines

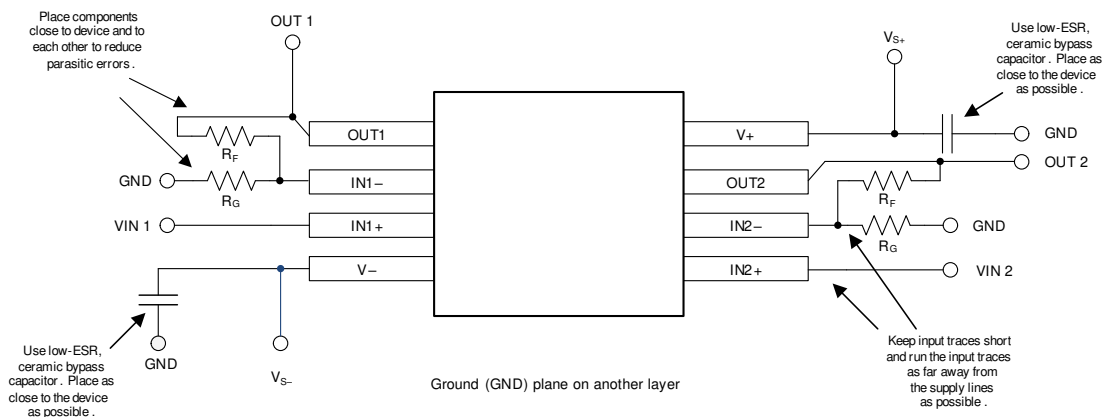
For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power connections of the board and propagate to the power pins of the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing a low-impedance path to ground.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is adequate for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace at a 90 degree angle is much better as opposed to running the traces in parallel with the noisy trace.
- Place the external components as close to the device as possible, as shown in  10-2. Keeping R_F and R_G close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

10.2 Layout Example



 10-1. Schematic Representation for Figure 10-2



 10-2. Layout Example

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [EMI Rejection Ratio of Operational Amplifiers](#)

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 サポート・リソース

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11.5 静電気放電に関する注意事項



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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

11.6 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMV321AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	2S3F	Samples
LMV321AQDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1N1	Samples
LMV321AUQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	2T7H	Samples
LMV324AQDRQ1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LM324Q	Samples
LMV324AQDYRQ1	ACTIVE	SOT-23-THIN	DYY	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324Q	Samples
LMV324AQPWRQ1	ACTIVE	TSSOP	PW	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324A	Samples
LMV358AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	27FT	Samples
LMV358AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L358AQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF LMV321A-Q1, LMV324A-Q1, LMV358A-Q1 :

- Catalog : [LMV321A](#), [LMV324A](#), [LMV358A](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

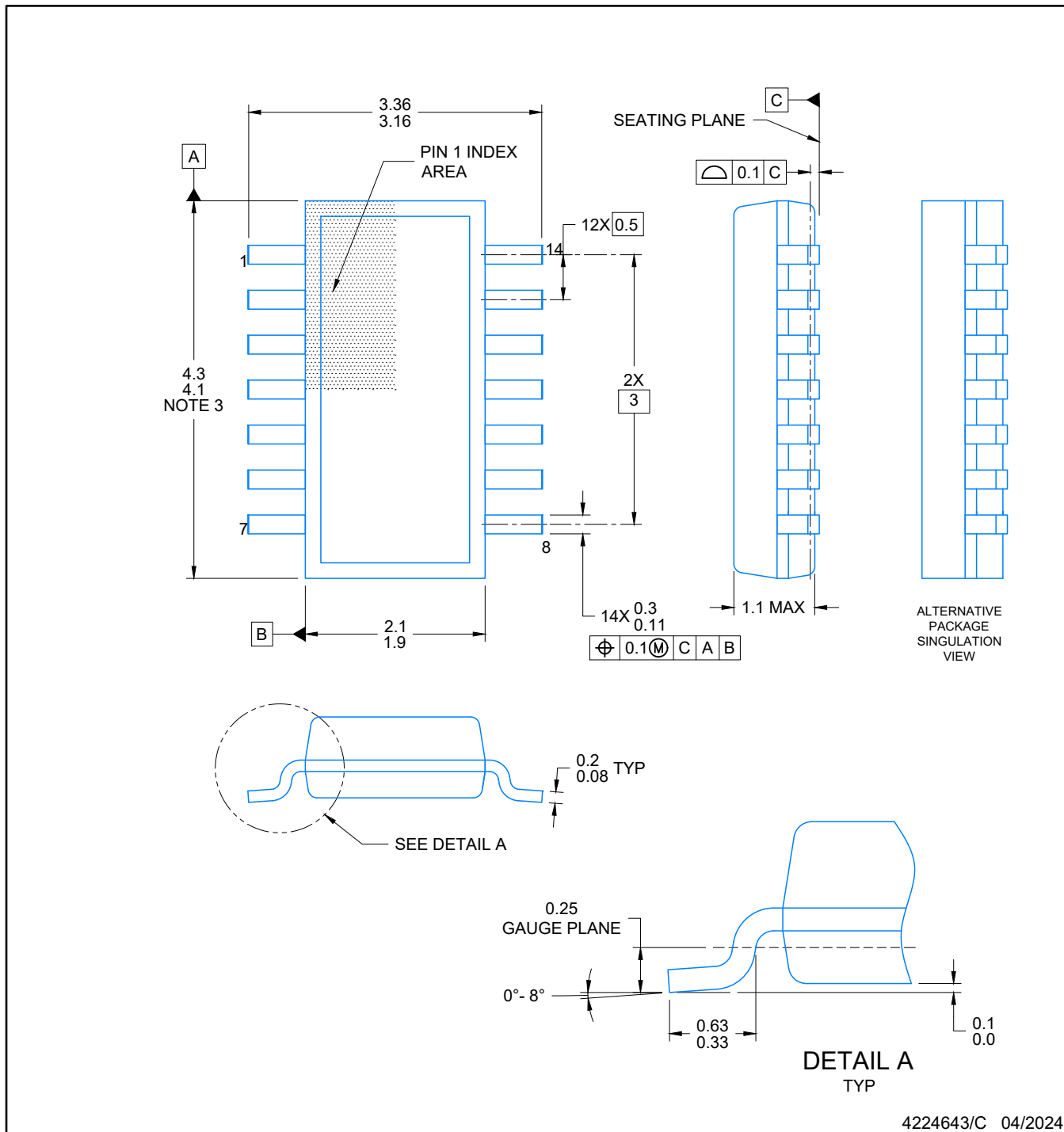
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321AQDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV324AQDRQ1	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LMV324AQDYRQ1	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
LMV324AQPWRQ1	TSSOP	PW	14	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



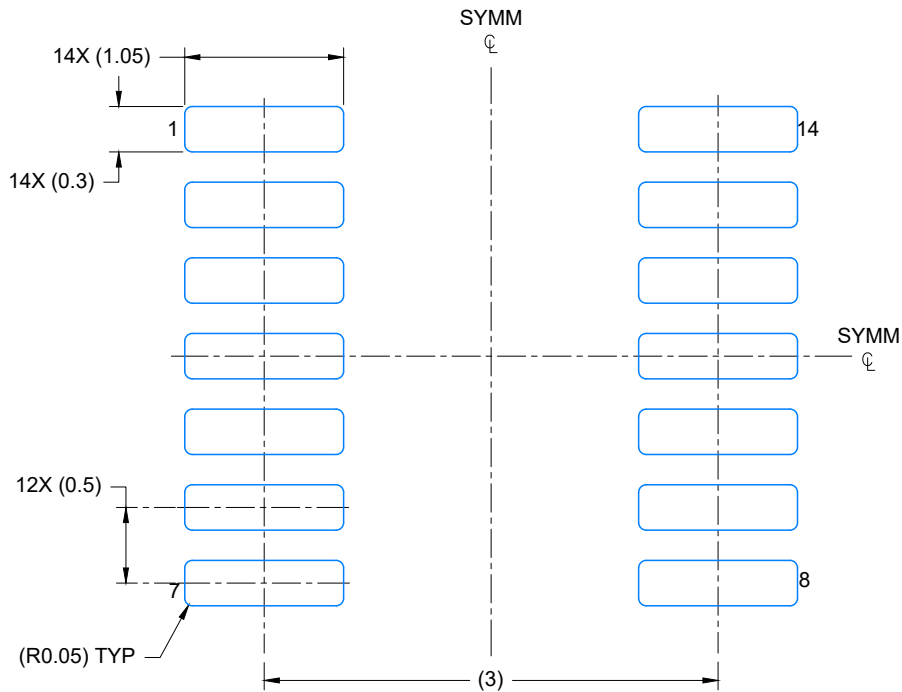
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321AQDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV324AQDRQ1	SOIC	D	14	2500	356.0	356.0	35.0
LMV324AQDYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
LMV324AQPWRQ1	TSSOP	PW	14	3000	356.0	356.0	35.0
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
LMV358AQDRQ1	SOIC	D	8	2500	356.0	356.0	35.0

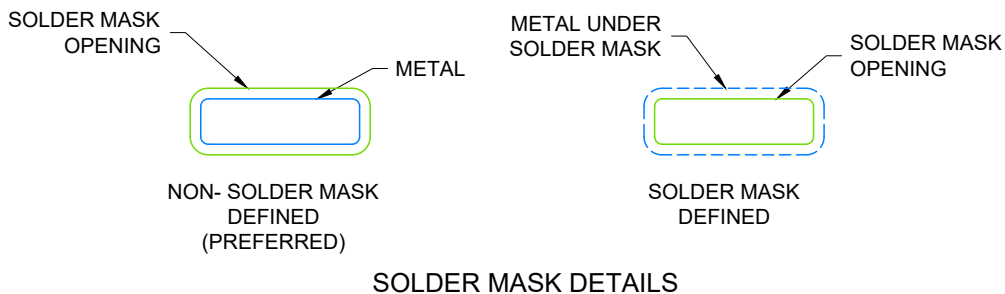


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB



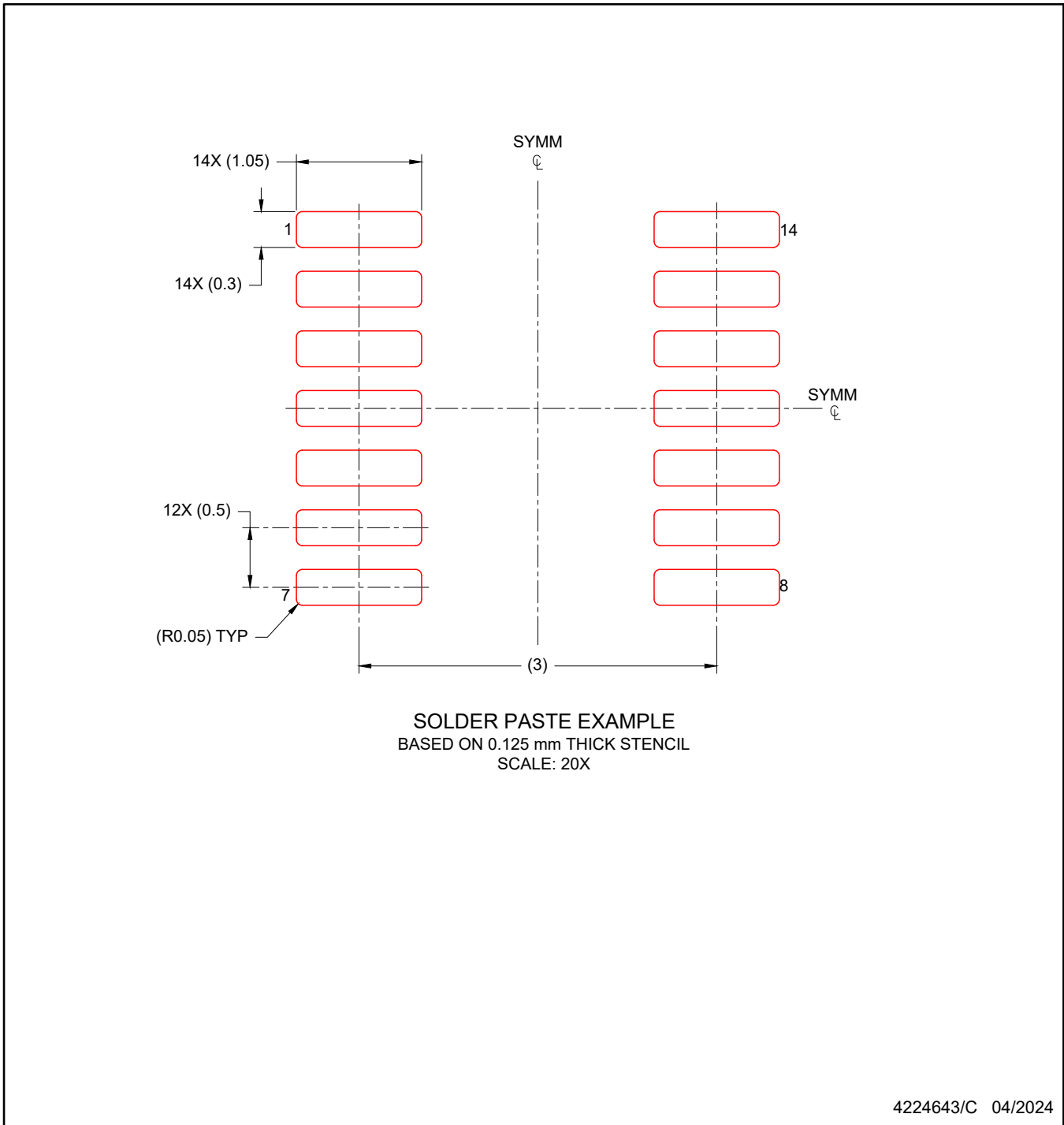
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224643/C 04/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

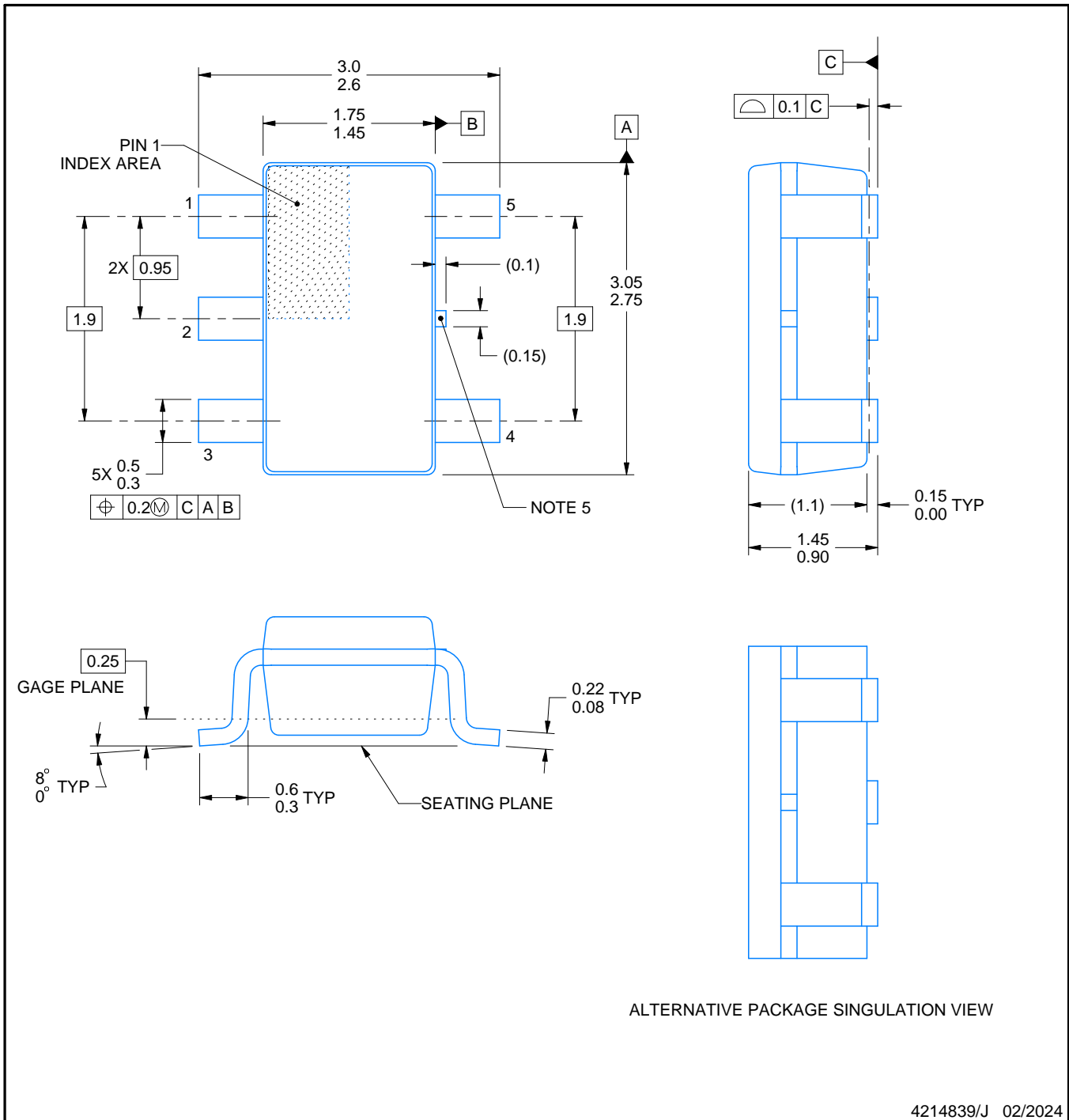
DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214839/J 02/2024

NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- Reference JEDEC MO-178.
- Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/J 02/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/J 02/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AB.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006$ [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

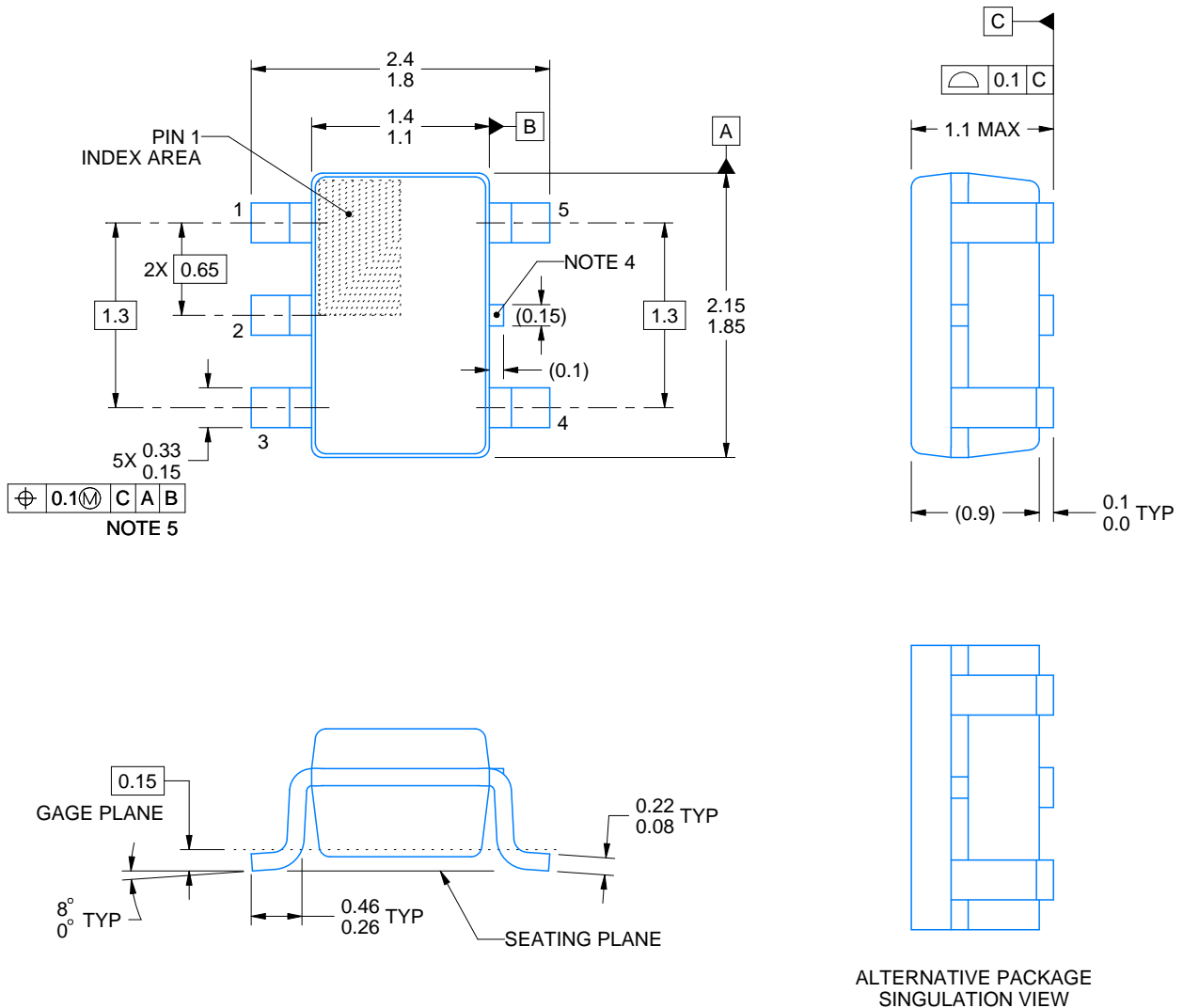
DCK0005A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/E 06/2024

NOTES:

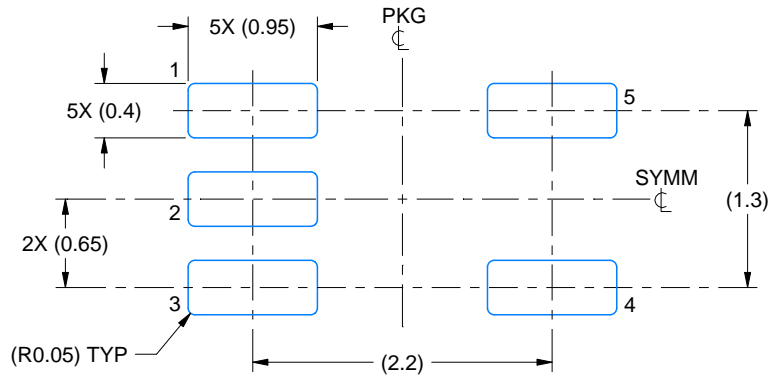
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

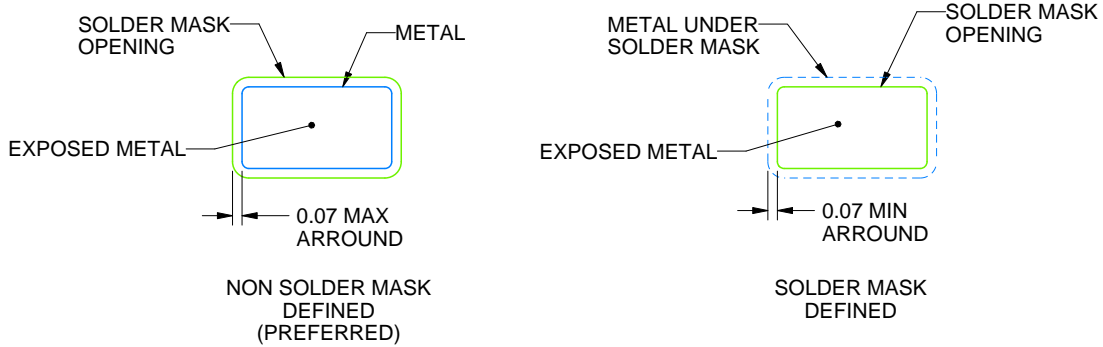
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/E 06/2024

NOTES: (continued)

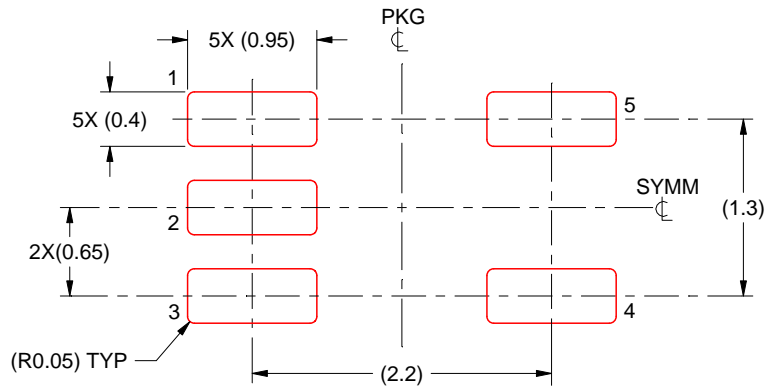
- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE: 18X

4214834/E 06/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

DGK0008A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES:

PowerPAD is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGK0008A

TM VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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